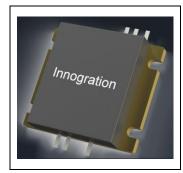
# Innogration (Suzhou) Co., Ltd. Document Number: S2MAH0407-70H3P

## 0.4-0.7GHz, 70W, 2 stages GaN Fully matched PA

## **Description**

The S2MAH0407-70H3P is a 70-watt Psat capable, 2 stage integrated IMFET, designed for broad band applications, with frequencies from 0.4 to 0.7GHz. The module is 50  $\Omega$  input/output matched and requires minimal external components, with DC block capacitor integrated inside When used at higher voltage like 32V, it can deliver up to 80W Psat across the full band The module implements multiple GaN active dice and its matching network within highly compact 30.8\*27.4mm metal RF package with excellent capability for heat dissipation.



 $V_{\text{DS}}\text{=}~28\text{V},\,V_{\text{gs1}}\text{=}~-3.2\text{V},\,I_{\text{dq1}}\text{=}200\text{mA},\,V_{\text{gs2}}\text{=}~-2.6\text{V},\,I_{\text{dq2}}\text{=}10\text{mA}$  ,Device screwed down

Freq (MHz)	P1(dBm)	P1 Gain (dB )	P3dB	P3dB	EFF (%)
			(dBm)	(W)	
400	47.29	33.8	48.14	65.2	51.7
450	48.00	34.1	48.61	72.7	50.7
500	47.79	33.2	48.59	72.3	47.5
550	48.26	33.1	49.22	83.5	49.9
600	48.94	34.3	49.83	96.2	57.1
650	47.44	34.8	48.34	68.2	52.1
700	48.20	33.7	49.42	87.6	68.5

### **Applications**

- P band power amplifier
- UHF power amplifier

**Table 1. Maximum Ratings** 

Rating	Symbol	Value	Unit
DrainSource Voltage	$V_{\scriptscriptstyle DSS}$	150	Vdc
GateSource Voltage	$V_{\sf GS}$	-10 to +2	Vdc
Operating Voltage	$V_{DD}$	+36	Vdc
Storage Temperature Range	Tstg	-65 to +150	°C
Case Operating Temperature	T <sub>c</sub>	+150	°C
Operating Junction Temperature	Τ <sub>J</sub>	+225	°C

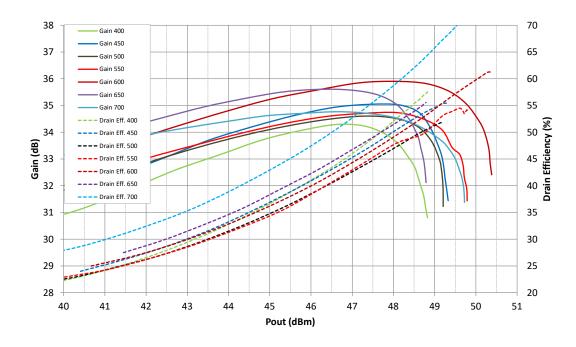


## TYPICAL CHARACTERISTICS

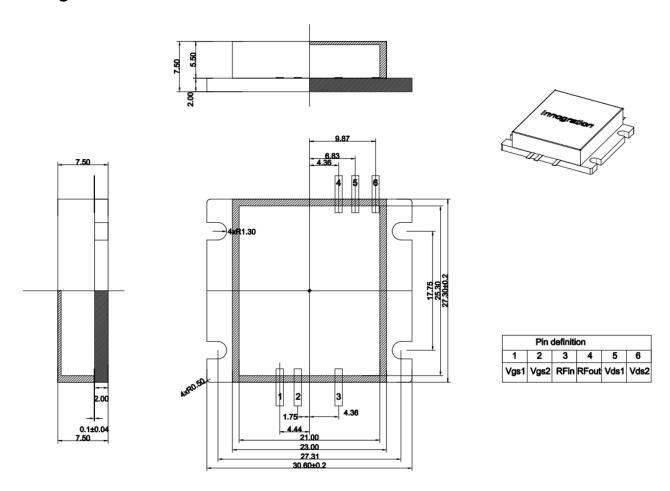
Figure 1. Network analyzer output S11/S21 (Pin=0dBm, Idq=200mA)



Figure 3. Pout, Eff, Gain, drain current Vs Frequency @28V



#### (Unit:mm) **Package Dimensions**



#### **Revision history**

Table 6. Document revision history

Date	Revision	Datasheet Status
2025/6/20	Rev 1.0	Advanced Datasheet

#### Application data based on HJ-25-07

#### **Disclaimers**

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